LN	lumber	Hits	Search Text	DB	Time stamp
3		29	(US-6144093-\$ or US-5821611-\$ or	USPAT;	2004/05/19 10:06
İ		,	US-4935803-\$ or US-6566164-\$ or	US-PGPUB	
			US-6528880-\$ or US-6521982-\$ or		
			US-6465276-\$ or US-6459147-\$ or		
1		ľ	US-6229196-\$ or US-6396127-\$ or		
	•		US-6319755-\$ or US-6307755-\$ or		'
		-	US-6256200-\$ or US-6255672-\$ or		
1		1	US-5841197-\$ or US-6249041-\$ or US-6249136-\$ or US-5814884-\$ or		
			US-6040626-\$ or US-5929523-\$ or		
	•		US-4989058-\$ or US-4199774-\$ or	0	
			US-5637922-\$ or US-5105536-\$ or		. :
1.			US-6421262-\$ or US-6282107-\$).did. or	1	1
			(US-20010000631-\$ or US-20030075796-\$ or	,	
1 .			US-20020093094-\$).did.		· .
4 `		1	6282107.URPN.	USPAT	2004/05/19 10:00
5		12	("4975821" "5126931" "5331533"	USPAT	2004/05/19 10:01
.			"5374857" "5434768" "5734563"		
	. يعد نا سا		_"5774350" 5805434" 5812383"		
6		ۋ ،	"5814884" "5886383" "5973939").PN. 4989058.URPN.		0004405455
7		11	4989058.0RPN. ("3788904" "4199774" "4250519"	USPAT	2004/05/19 10:04
.' .	.=	11	("3788904" "4199774" "4250519" "4270137" "4300152" "4300250"	USPAT	2004/05/19 10:04
'			"4358782" "4513309" "4633282"	, ,	
			"4639761" "4694313").PN:	* .	
8 .	•	3217	soi and mosfet	USPAT;	2004/05/19 10:06
	•.			US-PGPUB	2004/03/19 10:00
9	-	0	vaiable with threshold with voltage with	USPAT;	2004/05/19 10:07
'		•	complementary with mosfet	US-PGPUB;	
				EPO; JPO	
10	•	91	threshold with voltage with complementary	USPAT;	2004/05/19 10:28
			with mosfet	US-PGPUB;	
1,,		1520	1011	EPO; JPO	
11		1532	"91" and soi	USPAT;	2004/05/19 10:08
				US-PGPUB;	. [-
12		10	(threshold with voltage with complementary	EPO; JPO	2004/05/10 10 15
		. +0	with mosfet) and soi	USPAT; US-PGPUB;	2004/05/19 10:16
İ	,		with mobile of and bot	EPO; JPO	
13	-	81	(threshold with voltage with complementary	USPAT;	2004/05/19 10:16
			with mosfet) not ((threshold with voltage	US-PGPUB;	2004/05/15 10.10
			with complementary with mosfet) and soi)	EPO; JPO	
14		. 0	((threshold with voltage with	USPAT;	2004/05/19 10:17
.			complementary with mosfet) not ((threshold	US-PGPUB;	
	*		with voltage with complementary with	EPO; JPO	
l			mosfet) and soi)) and (adjusted near1	·	
15		45	bias)		0004/05/65
- ,	-	45	((threshold with voltage with complementary with mosfet) not ((threshold	USPAT;	2004/05/19 10:31
i			with voltage with complementary with	US-PGPUB;	
	(3)		mosfet) and soi)) and bias	EPO; JPO	
16		5434	threshold with voltage with mosfet	USPAT;	2004/05/19 10:28
	, .			US-PGPUB;	2004/03/19 10:28
	- 2-5			EPO; JPO	
17		95011	threshold near3 voltage near3mosfet	USPAT;	2004/05/19 10:29
	İ		1	US-PGPUB;	
				EPO; JPO	
18		3584	threshold near3 voltage near3 mosfet	USPAT;	2004/05/19 10:29
_ '	_		• •	US-PGPUB;	
19		582	/threshold many? 1t 2	EPO; JPO	
13		362	<pre>(threshold near3 voltage near3 mosfet) and (soi (silicon near1 insulation))</pre>	USPAT;	2004/05/19 10:30
	.		(SOI (SITICON HEART INSULATION))	US-PGPUB;	4 3 4 4
20		78	((threshold_near3_voltage_near3.mosfet)	EPO; JPO	2004/05/10 10 25
. = -		· • · · · · · · · · · · · · · · · ·	and (soi (silicon near1 insulation))) and	USPAT; US-PGPUB;	2004/05/19-10:31
			(second near1 mosfet)	EPO; JPO	
					

	200				
21		78	(((threshold near3 voltage near3 mosfet)	USPAT;	2004/05/19 10:31
		1	and (soi (silicon nearl insulation))) and	US-PGPUB;	
			(second near1 mosfet)) not (((threshold	EPO; JPO	٠.
'			with voltage with complementary with	ľ	•
			mosfet) not ((threshold with voltage with		*
			complementary with mosfet) and soi)) and		
			bias)		
22) :	42	(((threshold near3 voltage near3 mosfet)	USPAT;	2004/05/19 10:32
			and (soi (silicon nearl insulation))) and	US-PGPUB;	
		•	(second near1 mosfet)) and bias	EPO; JPO	<u>`</u> .
23	}	26	((((threshold near3 voltage near3 mosfet)	USPAT;	2004/05/19 10:32
			and (soi (silicon near1 insulation))) and	US-PGPUB;	
	i		(second near1 mosfet)) and bias) and (gate	EPO; JPO	
			adj electrode)		
24	,	17	5488243.URPN.	USPAT	2004/05/19 10:35
-25)	1707	(threshold near3 voltage near3 mosfet)	USPAT;	2004/05/19 10:45
			and bias	US-PGPUB;	
				EPO; JPO;	,
			·	DERWENT	
26	.0	3.6	((threshold near3_voltage near3_mosfet)	USPAT;	2004/05/19.10:46
1			and bias) and (partial\$3 near deplet\$3)	US-PGPUB;	,
	. ,	, -	, ,,	EPO; JPO;	
		* *		DERWENT	
27		27	(((threshold near3 voltage near3 mosfet)	USPAT;	2004/05/19 10:58
.			and bias) and (partial\$3 near deplet\$3))	US-PGPUB;	
	:		not ((((threshold near3 voltage near3	EPO; JPO;	
		1	mosfet) and (soi (silicon near)	DERWENT	
	•		insulation))) and (second near1 mosfet))	PHIMMINI	· . · .
	,		and bias)		
28		1. 0	6603175.URPN.	USPAT	2004/05/19 10:47
29		3.	("5818781" "6087893" "6160292"	USPAT	2004/05/19 10:47
23			"2001/0045602").PN.	OSFAI	2004/05/19 10:4/
30		51	partially near3 depleted near3 SOI near3	USPAT;	2004/05/10 14-21
130		1.	MOSFET	USPAT; US-PGPUB;	2004/05/19 14:21
			HOOFEI	EPO; JPO;	į ,
	•	. · · ·		DERWENT	
31		43	(partially near3 depleted near3 SOI near3	_	2004/05/19 13:16
1 31		1, 43	MOSFET) and (threshold near2 voltage)	USPAT;	2004/03/13 13:16
		1	noorm, and (threshold hearz voltage)	US-PGPUB;	
				EPO; JPO;	• •
32		. 8	6222234.URPN.	DERWENT USPAT	2004/05/19 13:10
33		2	6222234.URPN. ("5479033" "5827755").PN.		
35		0		USPAT	2004/05/19 13:11
33		-	6222234.pn. and (bias near electrode)	USPAT;	2004/05/19 13:16
4 .		1.		US-PGPUB;	
1				EPO; JPO;	
34		1	6222234.pn. and bias	DERWENT	2004/05/10 14:50
34	•	-	ozzzzał.pii. and bias	USPAT;	2004/05/19 14:59
1:				US-PGPUB;	
ľ				EPO; JPO;	
36		2	1164610071	DERWENT	0004/05/10 10 5-
130		2	"6461907"	USPAT;	2004/05/19 13:25
				US-PGPUB;	
1				EPO; JPO;	
		•	C4.C1.007, 177.713	DERWENT	· '
37		0	6461907.URPN.	USPAT	2004/05/19 13:26
38		6	("5081058" "5145802" "5479033"	USPAT	2004/05/19 13:26
1 ~ -			"5650339" "5728609" "5827755").PN.		
39		29	5479033.URPN.	USPAT	2004/05/19 13:28
40		. 1	6222234.pn. and ("n-channel" (n adj	USPAT;	2004/05/19 14:20
		. *	channel))	US-PGPUB;	
		, ,		EPO; JPO;	
				DERWENT	
41		0	6222234.pn. and ("p-channel" (p adj	USPAT;	2004/05/19 14:20
].			channel))	US-PGPUB;	
1			المناف المناف المناف المناف المناف المناف المناف المناف المناف المناف المناف المناف المناف المناف المناف المناف	EPO; JPO;	
			promise is a more some one of the first and them as the lot of the first of the first of the sound of the sou	DERWENT	. राज्यातः र । र रहेर्ग्यस्थाः व्यवस्थाः
-42		228	(partially fully) near3 depleted near3	USPAT;	2004/05/19 14:22
			MOSFET	US-PGPUB;	
				EPO; JPO;	
				DERWENT	*
		·			

-					
43		22	/ (Paranana) with restry means depreted nears	USPAT;	2004/05/19 14:59
	:	İ	MOSFET	US-PGPUB;	
İ				EPO; JPO;	
			W '	DERWENT	
44		21	((partially and fully) near3 depleted	USPAT;	2004/05/19 15:00
i		· ·	near3 MOSFET) and (p n)	US-PGPUB;	, , , , , , , , , , , , , , , , , , , ,
			·	EPO; JPO;	· ·
				DERWENT	1
45		128	(partially and fully) near3 depleted near3	USPAT;	2004/05/19 14:59
		,	SOI	US-PGPUB;	
	•	,		EPO; JPO;	
				DERWENT	*
46		436270	45and bias	USPAT;	2004/05/19 14:59
				US-PGPUB;	
				EPO; JPO;	
			* '	DERWENT]
47		4.0	((partially and fully) near3 depleted	USPAT;	2004/05/19 14:59
			near3 SOI) and bias	US-PGPUB;	
				EPO; JPO;	
-				DERWENT	
48		. 38	'''I'' and adaily' neers acpreced	USPAT:	2004/05/19 15:00
			near3 SOI) and bias) and (p n)	US-PGPUB;	1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 -
			·	EPO; JPO;	
			•	DERWENT	
49		22	(\P and rarry / noars	USPAT;	2004/05/19 15:00
		-8-	depleted near3 MOSFET)	US-PGPUB;	,,
			•	EPO; JPO;	
		,		DERWENT	
50		29	((((partially and fully) near3 depleted	USPAT;	2004/05/19 15:00
			near3 SOI) and bias) and (p n)) not	US-PGPUB;	
•	,	·	((partially and fully) near3 depleted	EPO; JPO;	
			near3 MOSFET)	DERWENT	